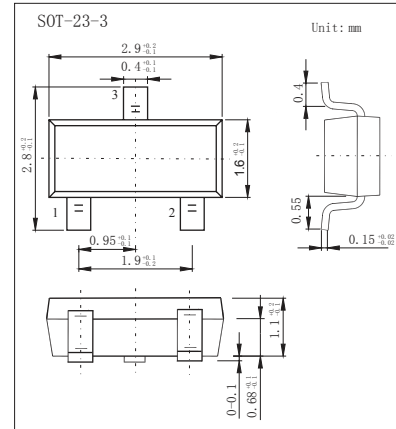
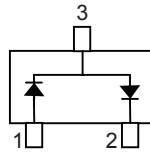


## Switching Diodes

## BAV99 (KAV99)

## ■ Features

- Small plastic SMD package.
- High switching speed: max.4 ns.
- Repetitive peak forward current: max.450 mA.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	$V_{RRM}$	85	V
Continuous reverse voltage	$V_R$	75	V
Continuous forward current (single diode loaded *) (double diode loaded *)	$I_F$	215 125	mA
Repetitive peak forward current	$I_{FRM}$	450	mA
Non-repetitive peak forward current $T_j=25^\circ\text{C}$ $t=1\mu\text{s}$	$I_{FSM}$	4	A
$t=1\text{ms}$		1	
$t=1\text{s}$		0.5	
power dissipation *	$P_D$	250	mW
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	360	K/W
Thermal resistance from junction to ambient *	$R_{th\ j\text{-}a}$	500	K/W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$

\* Device mounted on an FR4 printed-circuit board.

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

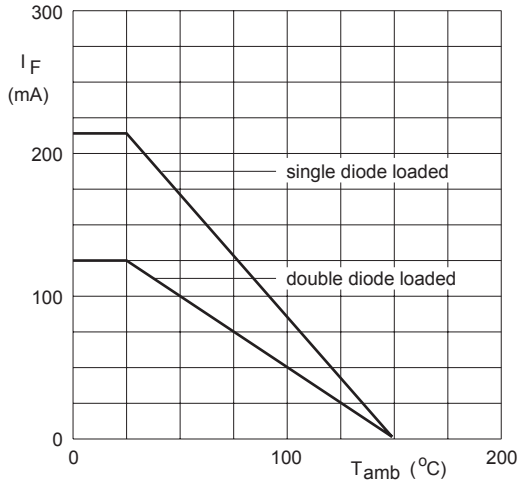
Parameter	Symbol	Test conditions	Max	Unit
Forward voltage	$V_F$	$I_F = 1\text{ mA}$	715	mV
		$I_F = 10\text{ mA}$	855	mV
		$I_F = 50\text{ mA}$	1	V
		$I_F = 150\text{ mA}$	1.25	V
Reverse current	$I_R$	$V_R = 75\text{ V}$	1	$\mu\text{ A}$
		$V_R = 25\text{ V}; T_j = 150^\circ\text{C}$	30	
		$V_R = 75\text{ V}; T_j = 150^\circ\text{C}$	50	
Diode capacitance	$C_d$	$V_R = 0\text{ V}, f = 1\text{ MHz}$	1.5	pF
Reverse recovery time	$t_{rr}$	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$	4	nS
Forward recovery voltage	$V_{fr}$	$I_F = 10\text{ mA}, t_r = 20\text{ ns}$	1.75	V

## ■ Marking

Marking	A7*
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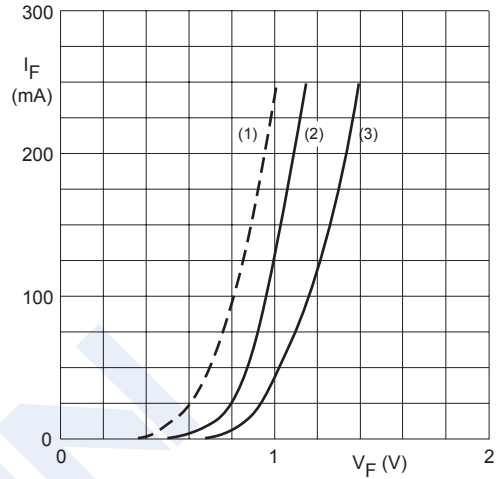
### BAV99 (KAV99)

■ Typical Characteristics



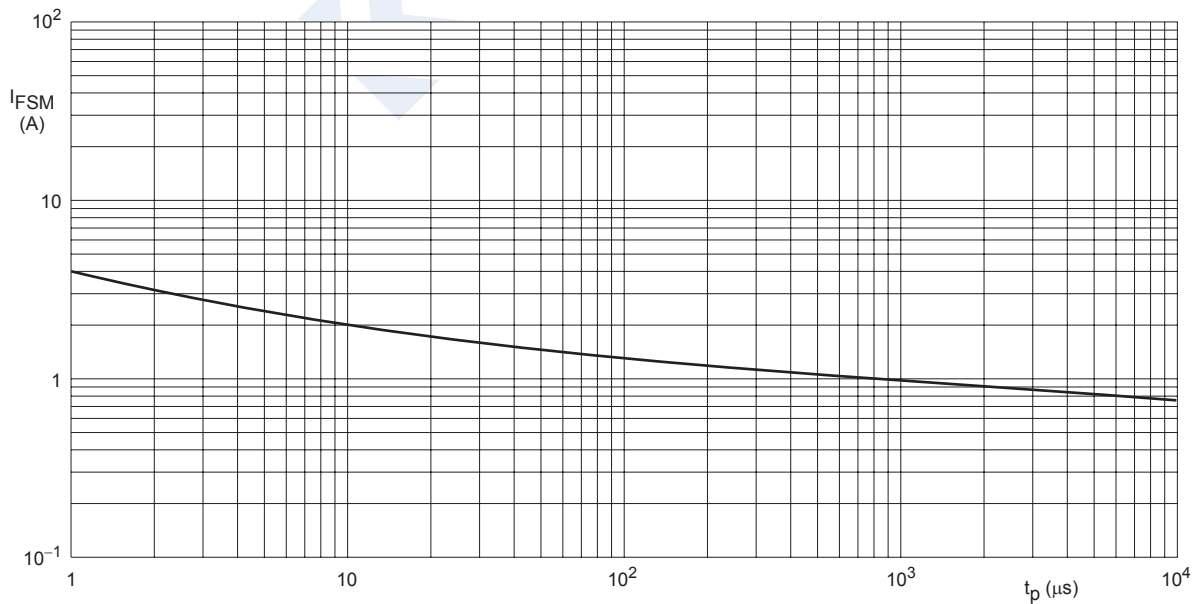
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_j = 150$  °C; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.  
 $T_j = 25$  °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

## BAV99 (KAV99)

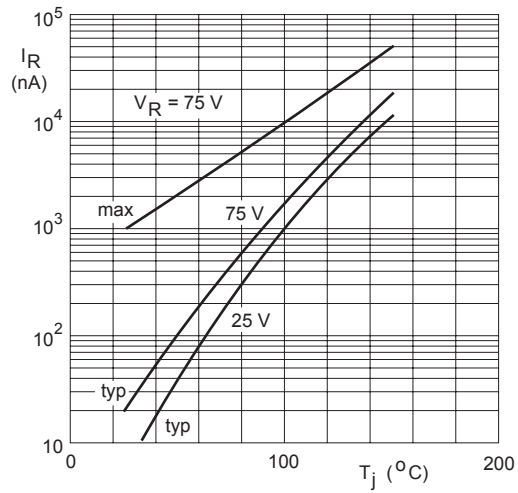
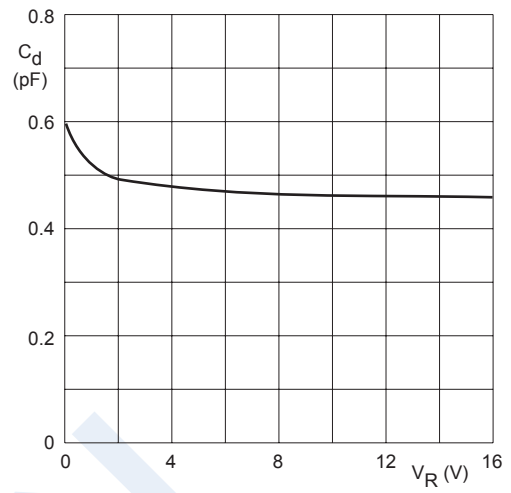


Fig.5 Reverse current as a function of junction temperature.



$f = 1\text{ MHz}$ ;  $T_j = 25\text{ }^{\circ}\text{C}$ .

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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